MC74LVX157

Quad 2-Channel Multiplexer

With 5 V−Tolerant Inputs

The MC74LVX157 is an advanced high speed CMOS quad 2−channel multiplexer. The inputs tolerate voltages up to 7.0 V, allowing the interface of 5.0 V systems to 3.0 V systems.

It consists of four 2−input digital multiplexers with common select (S) and enable ($\overline{E}$) inputs. When $\overline{E}$ is held High, selection of data is inhibited and all the outputs go Low.

The select decoding determines whether the I0 n or I1 n inputs get routed to the corresponding Z n outputs.

Features

- High Speed: t_{PD} = 5.1 ns (Typ) at V_{CC} = 3.3 V
- Low Power Dissipation: I_{CC} = 4 μA (Max) at T_A = 25°C
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Low Noise: V_{OLP} = 0.5 V (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance:
  - Human Body Model > 2000 V;
  - Machine Model > 200 V
- These Devices are Pb−Free and are RoHS Compliant

PIN NAMES

Pins	Function
I0n	Source 0 Data Inputs
I1n	Source 1 Data Inputs
$\overline{E}$	Enable Input
S	Select Input
Zn	Outputs

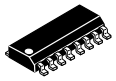
TRUTH TABLE

INPUTS				OUTPUT
$\overline{E}$	S	I0n	I1n	Zn
H	X	X	X	L
L	H	X	L	L
L	H	X	H	H
L	L	L	X	L
L	L	H	X	H

H = High Voltage Level; L = Low Voltage Level; X = High or Low Voltage Level ; For I_{CC} Reasons DO NOT FLOAT Inputs

ON Semiconductor®

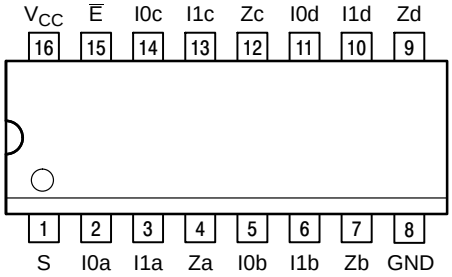
http://onsemi.com



SOIC−16
D SUFFIX
CASE 751B

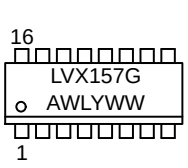
TSSOP−16
DT SUFFIX
CASE 948F

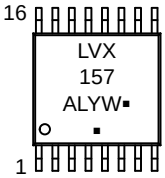
PIN ASSIGNMENT



16−Lead (Top View)

MARKING DIAGRAMS





SOIC−16 **TSSOP−16**

LVX157 = Specific Device Code
A = Assembly Location
WL, L = Wafer Lot
Y = Year
WW, W = Work Week
G or ▪ = Pb−Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

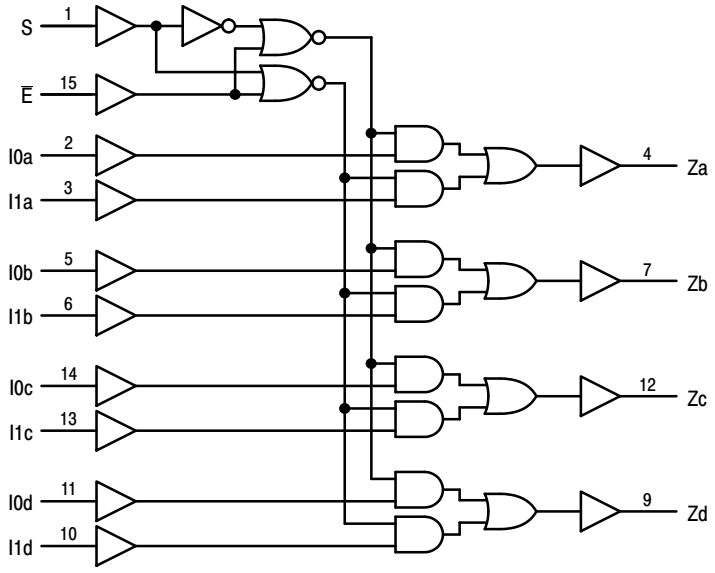


Figure 1. Logic Diagram

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	DC Supply Voltage	–0.5 to +7.0	V
V_{in}	DC Input Voltage	–0.5 to +7.0	V
V_{out}	DC Output Voltage	–0.5 to V_{CC} +0.5	V
I_{IK}	Input Diode Current	−20	mA
I_{OK}	Output Diode Current	±20	mA
I_{out}	DC Output Current, per Pin	±25	mA
I_{CC}	DC Supply Current, V_{CC} and GND Pins	±50	mA
P_D	Power Dissipation	180	mW
T_{stg}	Storage Temperature	–65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V_{CC}	DC Supply Voltage	2.0	3.6	V
V_{in}	DC Input Voltage	0	5.5	V
V_{out}	DC Output Voltage	0	V_{CC}	V
T_A	Operating Temperature, All Package Types	−40	+85	°C
$\Delta t/\Delta V$	Input Rise and Fall Time	0	100	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	V_{CC} V	T_A = 25°C			T_A = −40 to 85°C		Unit
				Min	Typ	Max	Min	Max	
V_{IH}	High−Level Input Voltage		2.0 3.0 3.6	1.5 2.0 2.4	− − −	− − −	1.5 2.0 2.4	− − −	V
V_{IL}	Low−Level Input Voltage		2.0 3.0 3.6	− − −	− − −	0.5 0.8 0.8	− − −	0.5 0.8 0.8	V
V_{OH}	High−Level Output Voltage (V_{in} = V_{IH} or V_{IL})	I_{OH} = −50μA I_{OH} = −50μA I_{OH} = −4mA	2.0 3.0 3.0	1.9 2.9 2.58	2.0 3.0	− − −	1.9 2.9 2.48	− − −	V
V_{OL}	Low−Level Output Voltage (V_{in} = V_{IH} or V_{IL})	I_{OL} = 50μA I_{OL} = 50μA I_{OL} = 4mA	2.0 3.0 3.0	− − −	0.0 0.0 −	0.1 0.1 0.36	− − −	0.1 0.1 0.44	V
I_{in}	Input Leakage Current	V_{in} = 5.5V or GND	3.6	−	−	±0.1	−	±1.0	μA
I_{CC}	Quiescent Supply Current	V_{in} = V_{CC} or GND	3.6	−	−	4.0	−	40.0	μA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AC ELECTRICAL CHARACTERISTICS (Input t_r = t_f = 3.0ns)

Symbol	Parameter	Test Conditions		T_A = 25°C			T_A = −40 to 85°C		Unit
				Min	Typ	Max	Min	Max	
t_{PLH}, t_{PHL}	Propagation Delay, Input to Output	V_{CC} = 2.7V	C_L = 15pF C_L = 50pF	− −	6.6 9.1	12.5 16.0	1.0 1.0	15.5 19.0	ns
		V_{CC} = 3.3 ± 0.3V	C_L = 15pF C_L = 50pF	− −	5.1 7.6	7.9 11.4	1.0 1.0	9.5 13.0	
t_{PLH}, t_{PHL}	Propagation Delay, S to Zn	V_{CC} = 2.7V	C_L = 15pF C_L = 50pF	− −	8.9 11.4	16.9 20.4	1.0 1.0	20.5 24.0	ns
		V_{CC} = 3.3 ± 0.3V	C_L = 15pF C_L = 50pF	− −	7.0 9.5	11.0 14.5	1.0 1.0	13.0 16.5	
t_{PLH}, t_{PHL}	Propagation Delay, $\overline{E}$ to Zn	V_{CC} = 2.7V	C_L = 15pF C_L = 50pF	− −	9.1 11.6	17.6 21.1	1.0 1.0	20.5 24.0	ns
		V_{CC} = 3.3 ± 0.3V	C_L = 15pF C_L = 50pF	− −	7.2 9.7	11.5 15.0	1.0 1.0	13.5 17.0	
t_{OSHL} t_{OSLH}	Output−to−Output Skew (Note 1)	V_{CC} = 2.7V V_{CC} = 3.3 ± 0.3V	C_L = 50pF C_L = 50pF	− −	− −	1.5 1.5	− −	1.5 1.5	ns

1. Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH−to−LOW (t_{OSHL}) or LOW−to−HIGH (t_{OSLH}); parameter guaranteed by design.

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	T_A = 25°C			T_A = −40 to 85°C		Unit
		Min	Typ	Max	Min	Max	
Cin	Input Capacitance	−	4	10	−	10	pF
C_{PD}	Power Dissipation Capacitance (Note 2)	−	20	−	−	−	pF

2. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}/4$ (per bit). C_{PD} is used to determine the no−load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.

NOISE CHARACTERISTICS (Input $t_r = t_f = 3.0$ns, $C_L = 50$pF, $V_{CC} = 3.3$V, Measured in SOIC Package)

Symbol	Characteristic	$T_A = 25°C$		Unit
		Typ	Max	
V_{OLP}	Quiet Output Maximum Dynamic V_{OL}	0.3	0.5	V
V_{OLV}	Quiet Output Minimum Dynamic V_{OL}	−0.3	−0.5	V
V_{IHD}	Minimum High Level Dynamic Input Voltage	−	2.0	V
V_{ILD}	Maximum Low Level Dynamic Input Voltage	−	0.8	V

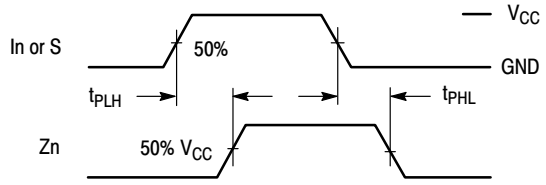


Figure 2.

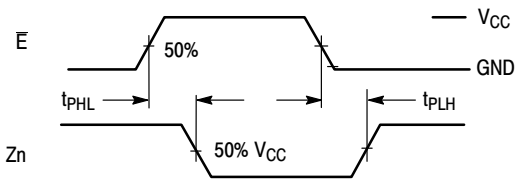
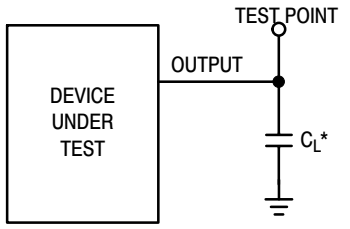


Figure 3.



*Includes all probe and jig capacitance

Figure 4. Propagation Delay Test Circuit

ORDERING INFORMATION

Device	Package	Shipping†
MC74LVX157DR2G	SOIC−16 (Pb−Free)	2500 Tape & Reel
MC74LVX157DTR2G	TSSOP−16 (Pb−Free)	2500 Tape & Reel

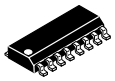
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

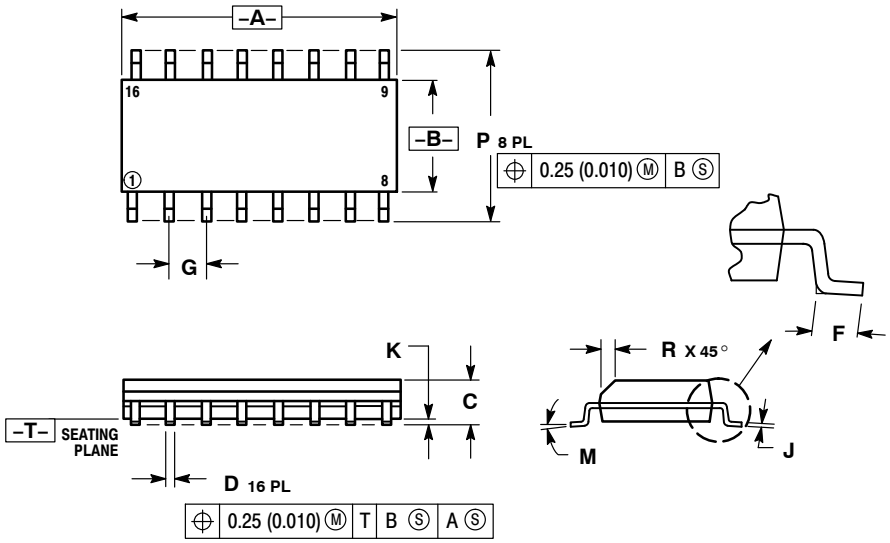
ON Semiconductor®

SOIC−16
CASE 751B−05
ISSUE K

DATE 29 DEC 2006



SCALE 1:1



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	9.80	10.00	0.386	0.393
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

STYLE 1:
PIN 1. COLLECTOR
2. BASE
3. EMITTER
4. NO CONNECTION
5. EMITTER
6. BASE
7. COLLECTOR
8. COLLECTOR
9. BASE
10. EMITTER
11. NO CONNECTION
12. EMITTER
13. BASE
14. COLLECTOR
15. EMITTER
16. COLLECTOR

STYLE 2:
PIN 1. CATHODE
2. ANODE
3. NO CONNECTION
4. CATHODE
5. CATHODE
6. NO CONNECTION
7. ANODE
8. CATHODE
9. CATHODE
10. ANODE
11. NO CONNECTION
12. CATHODE
13. CATHODE
14. NO CONNECTION
15. ANODE
16. CATHODE

STYLE 3:
PIN 1. COLLECTOR, DYE #1
2. BASE, #1
3. EMITTER, #1
4. COLLECTOR, #1
5. COLLECTOR, #2
6. BASE, #2
7. EMITTER, #2
8. COLLECTOR, #2
9. COLLECTOR, #3
10. BASE, #3
11. EMITTER, #3
12. COLLECTOR, #3
13. COLLECTOR, #4
14. BASE, #4
15. EMITTER, #4
16. COLLECTOR, #4

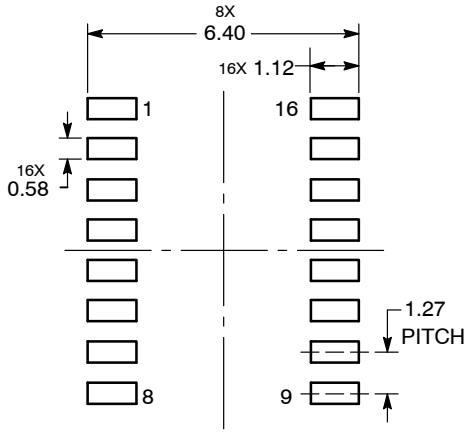
STYLE 4:
PIN 1. COLLECTOR, DYE #1
2. COLLECTOR, #1
3. COLLECTOR, #2
4. COLLECTOR, #2
5. COLLECTOR, #3
6. COLLECTOR, #3
7. COLLECTOR, #4
8. COLLECTOR, #4
9. BASE, #4
10. EMITTER, #4
11. BASE, #3
12. EMITTER, #3
13. BASE, #2
14. EMITTER, #2
15. BASE, #1
16. EMITTER, #1

STYLE 5:
PIN 1. DRAIN, DYE #1
2. DRAIN, #1
3. DRAIN, #2
4. DRAIN, #2
5. DRAIN, #3
6. DRAIN, #3
7. DRAIN, #4
8. DRAIN, #4
9. GATE, #4
10. SOURCE, #4
11. GATE, #3
12. SOURCE, #3
13. GATE, #2
14. SOURCE, #2
15. GATE, #1
16. SOURCE, #1

STYLE 6:
PIN 1. CATHODE
2. CATHODE
3. CATHODE
4. CATHODE
5. CATHODE
6. CATHODE
7. CATHODE
8. CATHODE
9. ANODE
10. ANODE
11. ANODE
12. ANODE
13. ANODE
14. ANODE
15. ANODE
16. ANODE

STYLE 7:
PIN 1. SOURCE N-CH
2. COMMON DRAIN (OUTPUT)
3. COMMON DRAIN (OUTPUT)
4. GATE P-CH
5. COMMON DRAIN (OUTPUT)
6. COMMON DRAIN (OUTPUT)
7. COMMON DRAIN (OUTPUT)
8. SOURCE P-CH
9. SOURCE P-CH
10. COMMON DRAIN (OUTPUT)
11. COMMON DRAIN (OUTPUT)
12. COMMON DRAIN (OUTPUT)
13. GATE N-CH
14. COMMON DRAIN (OUTPUT)
15. COMMON DRAIN (OUTPUT)
16. SOURCE N-CH

SOLDERING FOOTPRINT



DIMENSIONS: MILLIMETERS

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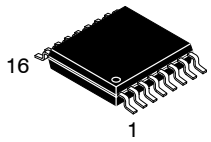
DESCRIPTION:	SOIC−16	PAGE 1 OF 1

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

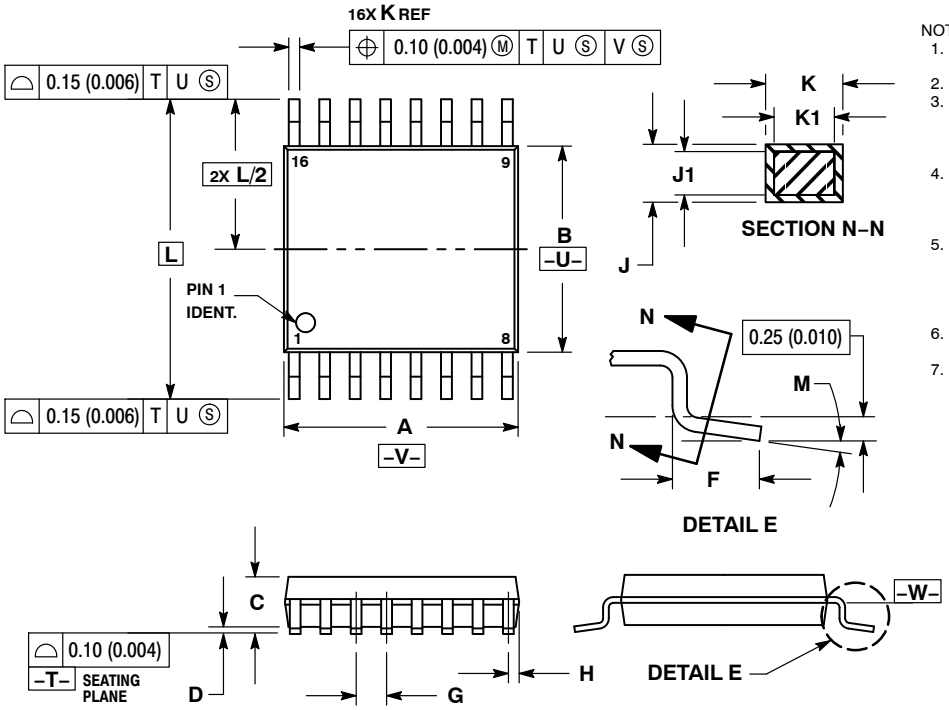
ON Semiconductor®



SCALE 2:1

TSSOP−16
CASE 948F−01
ISSUE B

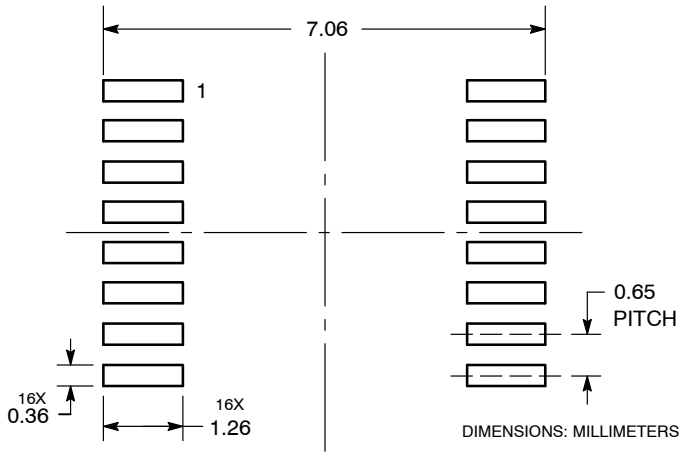
DATE 19 OCT 2006



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE −W−.

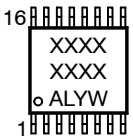
	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	−−−	1.20	−−−	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.18	0.28	0.007	0.011
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0 °	8 °	0 °	8 °

SOLDERING FOOTPRINT



DIMENSIONS: MILLIMETERS

GENERIC MARKING DIAGRAM*



XXXX	= Specific Device Code
A	= Assembly Location
L	= Wafer Lot
Y	= Year
W	= Work Week
G or ▪	= Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present.

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PUBLICATION ORDERING INFORMATION

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onsemi Website: www.onsemi.com

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North American Technical Support:
Voice Mail: 1 800−282−9855 Toll Free USA/Canada
Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:
Phone: 00421 33 790 2910
For additional information, please contact your local Sales Representative

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